

## ● FEATURES

Power dissipation

$P_D$ : 150 mW ( $T_{amb}=25^\circ\text{C}$ )

Forward Current

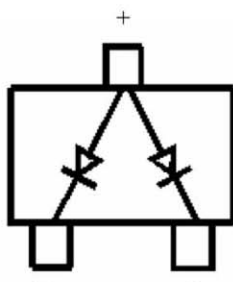
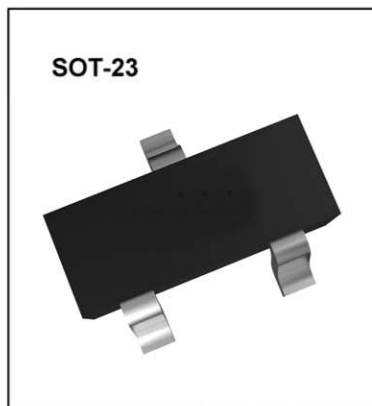
$I_F$ : 300 mA

Reverse Voltage

$V_R$ : 50 V

Operating and storage junction temperature range

$T_J, T_{stg}$ :  $-55^\circ\text{C}$  to  $+150^\circ\text{C}$



Marking: A41

## ● ELECTRICAL CHARACTERISTICS ( $T_{amb}=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)}$	$I_R=100\mu\text{A}$	50		V
Reverse voltage leakage current	$I_R$	$V_R=50\text{V}$		0.1	$\mu\text{A}$
Forward voltage	$V_F$	$I_F=10\text{mA}$		0.9	V
		$I_F=50\text{mA}$		1	
		$I_F=100\text{mA}$		1.2	
Diode capacitance	$C_D$	$V_R=0\text{V}, f=1\text{MHz}$		4	pF
Reverse recovery time	$t_{rr}$	$I_F=I_R=10\text{mA}, I_{RR}=0.1\times I_R$		4	nS